Dae Hwan Kim

List of Publications by Citations

136 papers	2,153 citations	25 h-index	41 g-index
138 ext. papers	2,484 ext. citations	3.7 avg, IF	4.66 L-index

#	Paper	IF	Citations
136	Extraction of Subgap Density of States in Amorphous InGaZnO Thin-Film Transistors by Using Multifrequency Capacitance–Voltage Characteristics. *IEEE Electron Device Letters*, **2010**, 31, 231-233	4.4	127
135	Highly stable transparent amorphous oxide semiconductor thin-film transistors having double-stacked active layers. *Advanced Materials*, **2010**, 22, 5512-6	24	113
134	Transparent, Flexible Strain Sensor Based on a Solution-Processed Carbon Nanotube Network. *ACS Applied Materials & Interfaces*, **2017**, 9, 26279-26285	9.5	97
133	Instability of amorphous oxide semiconductors via carrier-mediated structural transition between disorder and peroxide state. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 1277-1281	1.3	97
132	Effect of channel thickness on density of states in amorphous InGaZnO thin film transistor. *Applied Physics Letters*, **2011**, 98, 122105	3.4	89
131	Modeling of amorphous InGaZnO thin-film transistors based on the density of states extracted from the optical response of capacitance-voltage characteristics. *Applied Physics Letters*, **2008**, 93, 182102	3.4	84
130	Study on the photoresponse of amorphous In-Ga-Zn-O and zinc oxynitride semiconductor devices by the extraction of sub-gap-state distribution and device simulation. *ACS Applied Materials & Interfaces*, **2015**, 7, 15570-7	9.5	65
129	Synaptic Plasticity Selectively Activated by Polarization-Dependent Energy-Efficient Ion Migration in an Ultrathin Ferroelectric Tunnel Junction. *Nano Letters*, **2017**, 17, 1949-1955	11.5	62
128	Impact of Oxygen Flow Rate on the Instability Under Positive Bias Stresses in DC-Sputtered Amorphous InGaZnO Thin-Film Transistors. *IEEE Electron Device Letters*, **2012**, 33, 62-64	4.4	57
127	Subgap Density-of-States-Based Amorphous Oxide Thin Film Transistor Simulator (DeAOTS). *IEEE Transactions on Electron Devices*, **2010**, 57, 2988-3000	2.9	55
126	Amorphous InGaZnO Thin-Film Transistors—Part I: Complete Extraction of Density of States Over the Full Subband-Gap Energy Range. *IEEE Transactions on Electron Devices*, **2012**, 59, 2689-2698	2.9	49
125	Extraction of Density of States in Amorphous GaInZnO Thin-Film Transistors by Combining an Optical Charge Pumping and Capacitance–Voltage Characteristics. *IEEE Electron Device Letters*, **2008**, 29, 1292-1295	4.4	46
124	Cation composition effects on electronic structures of In-Sn-Zn-O amorphous semiconductors. *Journal of Applied Physics*, **2013**, 113, 183706	2.5	45
123	Density of states of amorphous In-Ga-Zn-O from electrical and optical characterization. *Journal of Applied Physics*, **2014**, 116, 154505	2.5	44
122	ZnO composite nanolayer with mobility edge quantization for multi-value logic transistors. *Nature Communications*, **2019**, 10, 1998	17.4	39
121	Differential Ideality Factor Technique for Extraction of Subgap Density of States in Amorphous InGaZnO Thin-Film Transistors. *IEEE Electron Device Letters*, **2012**, 33, 399-401	4.4	37
120	Origin of threshold voltage shift by interfacial trap density in amorphous InGaZnO thin film transistor under temperature induced stress. *Applied Physics Letters*, **2011**, 99, 062108	3.4	36

119	Synaptic devices based on two-dimensional layered single-crystal chromium thiophosphate (CrPS4). *NPG Asia Materials*, **2018**, 10, 23-30	10.3	35
118	10.2: Invited Paper: Development of Oxide TFTs Structures. *Digest of Technical Papers SID International Symposium*, **2013**, 44, 89-92	0.5	34
117	Electrical stress-induced instability of amorphous indium-gallium-zinc oxide thin-film transistors under bipolar ac stress. *Applied Physics Letters*, **2009**, 95, 132101	3.4	33
116	Systematic Decomposition of the Positive Bias Stress Instability in Self-Aligned Coplanar InGaZnO Thin-Film Transistors. *IEEE Electron Device Letters*, **2017**, 38, 580-583	4.4	30
115	Analytical Current and Capacitance Models for Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors. *IEEE Transactions on Electron Devices*, **2013**, 60, 3465-3473	2.9	27
114	Three-Dimensional Printed Poly(vinyl alcohol) Substrate with Controlled On-Demand Degradation for Transient Electronics. *ACS Nano*, **2018**, 12, 6006-6012	16.7	27
113	Low-frequency noise in amorphous indium-gallium-zinc oxide thin-film transistors from subthreshold to saturation. *Applied Physics Letters*, **2010**, 97, 122104	3.4	26
112	Effect of Oxygen Content on Current Stress-Induced Instability in Bottom-Gate Amorphous InGaZnO Thin-Film Transistors. *Materials*, **2019**, 12,	3.5	25
111	Investigation on the negative bias illumination stress-induced instability of amorphous indium-tin-zinc-oxide thin film transistors. *Applied Physics Letters*, **2014**, 105, 152108	3.4	24
110	High performance gallium-zinc oxynitride thin film transistors for next-generation display applications **2013**,		23
109	Modified Conductance Method for Extraction of Subgap Density of States in a-IGZO Thin-Film Transistors. *IEEE Electron Device Letters*, **2012**, 33, 1138-1140	4.4	22
108	Extraction of Separated Source and Drain Resistances in Amorphous Indium□Gallium□Zinc Oxide TFTs Through C□V Characterization. *IEEE Electron Device Letters*, **2011**, 32, 761-763	4.4	22
107	Complementary Silicon Nanowire Hydrogen Ion Sensor With High Sensitivity and Voltage Output. *IEEE Electron Device Letters*, **2012**, 33, 1768-1770	4.4	21
106	Experimental decomposition of the positive bias temperature stress-induced instability in self-aligned coplanar InGaZnO thin-film transistors and its modeling based on the multiple stretched-exponential functions. *Journal of the Society for Information Display*, **2017**, 25, 98-107	2.1	19
105	Origin of instability by positive bias stress in amorphous Si-In-Zn-O thin film transistor. *Applied Physics Letters*, **2011**, 99, 172106	3.4	18
104	Unified Subthreshold Coupling Factor Technique for Surface Potential and Subgap Density-of-States in Amorphous Thin Film Transistors. *IEEE Electron Device Letters*, **2013**, 34, 641-643	4.4	17
103	Production of □-carotene by recombinant Escherichia coli with engineered whole mevalonate pathway in batch and fed-batch cultures. *Biotechnology and Bioprocess Engineering*, **2009**, 14, 559-564	3.1	17
102	7-4: Invited Paper: Internal Compensation Type OLED Display Using High Mobility Oxide TFT. *Digest of Technical Papers SID International Symposium*, **2017**, 48, 76-79	0.5	16

101	P-3: A Study on the Hot Carrier Effect in InGaZnO Thin Film Transistors. *Digest of Technical Papers SID International Symposium*, **2019**, 50, 1222-1225	0.5	16
100	Effect of direct current sputtering power on the behavior of amorphous indium-gallium-zinc-oxide thin-film transistors under negative bias illumination stress: A combination of experimental analyses and device simulation. *Applied Physics Letters*, **2015**, 106, 123505	3.4	16
99	Effect of oxygen content of the LaAlO 3 layer on the synaptic behavior of Pt/LaAlO 3 /Nb-doped SrTiO 3 memristors for neuromorphic applications. *Solid-State Electronics*, **2018**, 140, 139-143	1.7	16
98	Ultrasensitive Electrical Detection of Hemagglutinin for Point-of-Care Detection of Influenza Virus Based on a CMP-NANA Probe and Top-Down Processed Silicon Nanowire Field-Effect Transistors. *Sensors*, **2019**, 19,	3.8	16
97	The Effect of Gate and Drain Fields on the Competition Between Donor-Like State Creation and Local Electron Trapping in InGaZnO Thin Film Transistors Under Current Stress. *IEEE Electron Device Letters*, **2015**, 36, 1336-1339	4.4	16
96	Dual-Sweep Combinational Transconductance Technique for Separate Extraction of Parasitic Resistances in Amorphous Thin-Film Transistors. *IEEE Electron Device Letters*, **2015**, 36, 144-146	4.4	15
95	Fabrication of InGaAs-on-Insulator Substrates Using Direct Wafer-Bonding and Epitaxial Lift-Off Techniques. *IEEE Transactions on Electron Devices*, **2017**, 64, 3601-3608	2.9	15
94	Characterization of density-of-states and parasitic resistance in a-InGaZnO thin-film transistors after negative bias stress. *Applied Physics Letters*, **2013**, 102, 143502	3.4	15
93	The Effect of the Active Layer Thickness on the Negative Bias Stress-Induced Instability in Amorphous InGaZnO Thin-Film Transistors. *IEEE Electron Device Letters*, **2011**, 32, 1388-1390	4.4	15
92	Comparative study of quasi-static and normal capacitance–voltage characteristics in amorphous Indium-Gallium-Zinc-Oxide thin film transistors. *Solid-State Electronics*, **2011**, 56, 95-99	1.7	14
91	Impact of Ground Plane Doping and Bottom-Gate Biasing on Electrical Properties in In0.53Ga0.47As-OI MOSFETs and Donor Wafer Reusability Toward Monolithic 3-D Integration With In0.53Ga0.47As Channel. *IEEE Transactions on Electron Devices*, **2018**, 65, 1862-1868	2.9	13
90	Investigation of Carrier Transport Mechanism in High Mobility ZnON Thin-Film Transistors. *IEEE Electron Device Letters*, **2016**, 37, 1570-1573	4.4	13
89	SiNW-CMOS Hybrid Common-Source Amplifier as a Voltage-Readout Hydrogen Ion Sensor. *IEEE Electron Device Letters*, **2013**, 34, 135-137	4.4	13
88	Enhanced sensing of gas molecules by a 99.9% semiconducting carbon nanotube-based field-effect transistor sensor. *Applied Physics Letters*, **2017**, 111, 022102	3.4	12
87	Method to Extract Interface and Bulk Trap Separately Over the Full Sub-Gap Range in Amorphous InGaZnO Thin-Film Transistors by Using Various Channel Thicknesses. *IEEE Electron Device Letters*, **2019**, 40, 574-577	4.4	12
86	Hybrid complementary inverter based on carbon nanotube and IGZO thin-film transistors with controlled process conditions. *Journal of Alloys and Compounds*, **2018**, 762, 456-462	5.7	12
85	Semiconducting carbon nanotube network thin-film transistors with enhanced inkjet-printed source and drain contact interfaces. *Applied Physics Letters*, **2017**, 111, 173108	3.4	11
84	Control of the Boundary between the Gradual and Abrupt Modulation of Resistance in the Schottky Barrier Tunneling-Modulated Amorphous Indium-Gallium-Zinc-Oxide Memristors for Neuromorphic Computing. *Electronics (Switzerland)*, **2019**, 8, 1087	2.6	11

83	Experimental extraction of stern-layer capacitance in biosensor detection using silicon nanowire field-effect transistors. *Current Applied Physics*, **2020**, 20, 828-833	2.6	11
82	Highly transparent tactile sensor based on a percolated carbon nanotube network. *AIP Advances*, **2018**, 8, 065109	1.5	11
81	Digital and Analog Switching Characteristics of InGaZnO Memristor Depending on Top Electrode Material for Neuromorphic System. *IEEE Access*, **2020**, 8, 192304-192311	3.5	11
80	Ink-jet printed semiconducting carbon nanotube ambipolar transistors and inverters with chemical doping technique using polyethyleneimine. *Applied Physics Letters*, **2016**, 109, 263103	3.4	11
79	Effect of Simultaneous Mechanical and Electrical Stress on the Electrical Performance of Flexible In-Ga-Zn-O Thin-Film Transistors. *Materials*, **2019**, 12,	3.5	10
78	Bias-Dependent Effective Channel Length for Extraction of Subgap DOS by Capacitance–Voltage Characteristics in Amorphous Semiconductor TFTs. *IEEE Transactions on Electron Devices*, **2015**, 62, 2689-2694	2.9	10
77	Effect of interface states on the instability under temperature stress in amorphous SiInZnO thin film transistor. *Applied Physics Letters*, **2011**, 99, 162101	3.4	10
76	A novel fabrication method for co-integrating ISFET with damage-free sensing oxide and threshold voltage-tunable CMOS read-out circuits. *Sensors and Actuators B: Chemical*, **2018**, 260, 627-634	8.5	9
75	A Study on the Degradation of In-Ga–Zn-O Thin-Film Transistors Under Current Stress by Local Variations in Density of States and Trapped Charge Distribution. *IEEE Electron Device Letters*, **2015**, 36, 690-692	4.4	9
74	One Transistor–Two Memristor Based on Amorphous Indium–Gallium–Zinc-Oxide for Neuromorphic Synaptic Devices. *ACS Applied Electronic Materials*, **2020**, 2, 2837-2844	4	9
73	Drift-Free pH Detection With Silicon Nanowire Field-Effect Transistors. *IEEE Electron Device Letters*, **2016**, 37, 652-655	4.4	9
72	Effect of the Gate Dielectric Layer of Flexible InGaZnO Synaptic Thin-Film Transistors on Learning Behavior. *ACS Applied Electronic Materials*, **2021**, 3, 3972-3979	4	9
71	Implementing an artificial synapse and neuron using a Si nanowire ion-sensitive field-effect transistor and indium-gallium-zinc-oxide memristors. *Sensors and Actuators B: Chemical*, **2019**, 296, 126616	8.5	8
70	The Calculation of Negative Bias Illumination Stress-Induced Instability of Amorphous InGaZnO Thin-Film Transistors for Instability-Aware Design. *IEEE Transactions on Electron Devices*, **2018**, 65, 1002-1008	2.9	8
69	The electron trap parameter extraction-based investigation of the relationship between charge trapping and activation energy in IGZO TFTs under positive bias temperature stress. *Solid-State Electronics*, **2018**, 140, 90-95	1.7	8
68	Modeling and Separate Extraction of Gate-Bias- and Channel-Length-Dependent Intrinsic and Extrinsic Source–Drain Resistances in MOSFETs. *IEEE Electron Device Letters*, **2011**, 32, 722-724	4.4	8
67	Pd/IGZO/p+-Si Synaptic Device with Self-Graded Oxygen Concentrations for Highly Linear Weight Adjustability and Improved Energy Efficiency. *ACS Applied Electronic Materials*, **2020**, 2, 2390-2397	4	8
66	Complementary Hybrid Semiconducting Superlattices with Multiple Channels and Mutual Stabilization. *Nano Letters*, **2020**, 20, 4864-4871	11.5	7

65	Hybrid Open Drain Method and Fully Current-Based Characterization of Asymmetric Resistance Components in a Single MOSFET. *IEEE Transactions on Electron Devices*, **2016**, 63, 4196-4200	2.9	7
64	Production of β-carotene and acetate in recombinant Escherichia coli with or without mevalonate pathway at different culture temperature or pH. *Biotechnology and Bioprocess Engineering*, **2012**, 17, 1196-1204	3.1	7
63	Separate Extraction of Source, Drain, and Substrate Resistances in MOSFETs With Parasitic Junction Current Method. *IEEE Electron Device Letters*, **2010**,	4.4	7
62	Observation of Hydrogen-Related Defect in Subgap Density of States and Its Effects Under Positive Bias Stress in Amorphous InGaZnO TFT. *IEEE Electron Device Letters*, **2021**, 42, 708-711	4.4	7
61	. *IEEE Electron Device Letters*, **2017**, 38, 584-587	4.4	6
60	Flexible carbon nanotube Schottky diode and its integrated circuit applications.. *RSC Advances*, **2019**, 9, 22124-22128	3.7	6
59	A novel SiNW/CMOS hybrid biosensor for high sensitivity/low noise **2013**,		6
58	Oxygen Content and Bias Influence on Amorphous InGaZnO TFT-Based Temperature Sensor Performance. *IEEE Electron Device Letters*, **2019**, 40, 1666-1669	4.4	5
57	Modeling and Separate Extraction Technique for Gate Bias-Dependent Parasitic Resistances and Overlap Length in MOSFETs. *IEEE Transactions on Electron Devices*, **2015**, 62, 1063-1067	2.9	5
56	Total Subgap Range Density of States-Based Analysis of the Effect of Oxygen Flow Rate on the Bias Stress Instabilities in a-IGZO TFTs. *IEEE Transactions on Electron Devices*, **2021**, 1-8	2.9	5
55	Humidity Effects According to the Type of Carbon Nanotubes. *IEEE Access*, **2021**, 9, 6810-6816	3.5	5
54	21-4: Distinguished Paper: Experimental Decomposition of the Positive Bias Temperature Stress-induced Instability in Self-aligned Coplanar InGaZnO Thin-film Transistors and its Modeling based on the Multiple Stretched-exponential Functions. *Digest of Technical Papers SID International Symposium*, **2017**, 48, 298-301	0.5	4
53	. *IEEE Electron Device Letters*, **2019**, 40, 40-43	4.4	4
52	Hybrid integration of carbon nanotube and amorphous IGZO thin-film transistors. *AIP Advances*, **2020**, 10, 025131	1.5	4
51	Effect of liquid gate bias rising time in pH sensors based on Si nanowire ion sensitive field effect transistors. *Solid-State Electronics*, **2018**, 140, 109-114	1.7	4
50	Comprehensive separate extraction of parasitic resistances in MOSFETs considering the gate bias-dependence and the asymmetric overlap length. *Microelectronics Reliability*, **2018**, 85, 66-70	1.2	4
49	. *IEEE Electron Device Letters*, **2019**, 40, 1431-1434	4.4	4
48	Extraction of the Channel Mobility in InGaZnO TFTs Using Multifrequency Capacitance–Voltage Method. *IEEE Electron Device Letters*, **2012**, 33, 815-817	4.4	4

47	Excessive Oxygen Peroxide Model-Based Analysis of Positive-Bias-Stress and Negative-Bias-Illumination-Stress Instabilities in Self-Aligned Top-Gate Coplanar In□Ga□Zn□O Thin-Film Transistors. *Advanced Electronic Materials*,2101062	6.4	4
46	Universal model of bias-stress-induced instability in inkjet-printed carbon nanotube networks field-effect transistors. *Solid-State Electronics*, **2018**, 140, 80-85	1.7	3
45	Extraction of Propagation Delay-Correlated Mobility and Its Verification for Amorphous InGaZnO Thin-Film Transistor-Based Inverters. *IEEE Transactions on Electron Devices*, **2015**, 62, 1504-1510	2.9	3
44	Design of Noncoplanar Diagonal Electrode Structure for Oxide Thin-Film Transistor. *IEEE Electron Device Letters*, **2011**, 32, 39-41	4.4	3
43	Sub-1-V-Output CMOS bandgap reference circuit with small area and low power consumption. *IEICE Electronics Express*, **2009**, 6, 161-166	0.5	3
42	Hydrophobic Polymer Encapsulation Effects on Subgap Density of States in Multilayered Molybdenum Disulfide Field-Effect Transistors. *Physica Status Solidi - Rapid Research Letters*, **2020**, 14, 1900492	2.5	3
41	Positive Bias Stress Instability of InGaZnO TFTs With Self-Aligned Top-Gate Structure in the Threshold-Voltage Compensated Pixel. *IEEE Electron Device Letters*, **2020**, 41, 50-53	4.4	3
40	Analysis of Threshold Voltage Shift for Full V/V/Oxygen-Content Span under Positive Bias Stress in Bottom-Gate Amorphous InGaZnO Thin-Film Transistors. *Micromachines*, **2021**, 12,	3.3	3
39	Threshold-Variation-Tolerant Coupling-Gate □GZO Synaptic Transistor for More Reliably Controllable Hardware Neuromorphic System. *IEEE Access*, **2021**, 9, 59345-59352	3.5	3
38	Band-Bending Effect in the Characterization of Subgap Density-of-States in Amorphous TFTs Through Fully Electrical Techniques. *IEEE Electron Device Letters*, **2017**, 38, 199-202	4.4	2
37	Spectroscopic Influence of Virtual Reality and Augmented Reality Display Devices on the Human Nonvisual Characteristics and Melatonin Suppression Response. *IEEE Photonics Journal*, **2018**, 1-1	1.8	2
36	Extraction of the interface trap density through the differential subthreshold ideality factor technique in normally-off AlGaN/GaN MOSHFETs. *Journal of the Korean Physical Society*, **2015**, 66, 1291-1294	0.6	2
35	P-205L: Late-News Poster: Comparison between a-InGaZnO and a-InHfZnO TFTs in Perspective of Subgap Density of States (DOS) in Active Film. *Digest of Technical Papers SID International Symposium*, **2010**, 41, 1389	0.5	2
34	Channel width dependence of hot electron injection program/hot hole erase cycling behavior in silicon-oxide-nitride-oxide-silicon (SONOS) memories. *Solid-State Electronics*, **2008**, 52, 844-848	1.7	2
33	Influence of Al2O3 layer on InGaZnO memristor crossbar array for neuromorphic applications. *Chaos, Solitons and Fractals*, **2022**, 156, 111813	9.3	2
32	Alternating Current-Based Technique for Separate Extraction of Parasitic Resistances in MISFETs With or Without the Body Contact. *IEEE Electron Device Letters*, **2020**, 41, 1528-1531	4.4	2
31	Multiplexed Silicon Nanowire Tunnel FET-Based Biosensors With Optimized Multi-Sensing Currents. *IEEE Sensors Journal*, **2021**, 21, 8839-8846	4	2
30	Reliability-Aware SPICE Compatible Compact Modeling of IGZO Inverters on a Flexible Substrate. *Applied Sciences (Switzerland)*, **2021**, 11, 4838	2.6	2

29	SPICE compact model of IGZO memristor based on non-quasi statically updated Schottky barrier height **2019**,		2
28	. *IEEE Access*, **2021**, 9, 73090-73102	3.5	2
27	Effect of Hydrogen Migration in SiO2/Al2O3 Stacked Gate Insulator of InGaZnO Thin-Film Transistors. *Crystals*, **2022**, 12, 594	2.3	2
26	Analysis and Modeling on the pH-Dependent Current Drift of Si Nanowire Ion-Sensitive Field Effect Transistor (ISFET)-Based Biosensors. *Journal of Nanoscience and Nanotechnology*, **2017**, 17, 3146-3150	1.3	1
25	Influence of Nitrogen Content on Persistent Photoconductivity in Zinc Oxynitride Thin Film Transistors. *IEEE Electron Device Letters*, **2020**, 41, 561-564	4.4	1
24	Novel Fabrication Method for Forming Damage-Free Sensing Oxide and Threshold Voltage-Tunable Complementary Metal-Oxide Semiconductor in a pH Sensor-CMOS Hybrid System. *Journal of Nanoscience and Nanotechnology*, **2017**, 17, 8265-8270	1.3	1
23	19-3: Late-News Paper: Universal Method to Determine the Dynamic NBIS- and PBS-induced Instabilities on Self-aligned Coplanar InGaZnO Thin-film Transistors. *Digest of Technical Papers SID International Symposium*, **2018**, 49, 232-235	0.5	1
22	P-202L: Late-News Poster: Density-of-States Based Analysis on the Effect of Active Thin-film Thickness on Current Stress-induced Instability in Amorphous InGaZnO AMOLED Driver TFTs. *Digest of Technical Papers SID International Symposium*, **2011**, 42, 1223-1226	0.5	1
21	Wafer-scale carbon nanotube network transistors. *Nanotechnology*, **2020**, 31, 465303	3.4	1
20	Impact Ionization and Hot-Carrier Degradation in Saddle-Fin and Buried-Gate Transistor of Dynamic Random Access Memory at Cryogenic Temperature. *IEEE Electron Device Letters*, **2021**, 42, 653-656	4.4	1
19	Current-to-transconductance ratio technique for simultaneous extraction of threshold voltage and parasitic resistances in MOSFETs. *Solid-State Electronics*, **2021**, 183, 108133	1.7	1
18	Estimation of melatonin level and core body temperature: heart rate and heart rate variability as circadian rhythm markers. *Biological Rhythm Research*,1-18	0.8	0
17	Temperature and gate-bias-dependent charge transport in inkjet-printed polymer field-effect transistor. *Journal of the Korean Physical Society*, **2021**, 79, 1063-1068	0.6	0
16	Density-of-States-Based Physical Model for Ink-Jet Printed Thiophene Polymeric TFTs. *IEEE Transactions on Electron Devices*, **2020**, 67, 283-288	2.9	0
15	A highly reliable physics-based SPICE compact model of IGZO memristor considering the dependence on electrode metals and deposition sequence. *Solid-State Electronics*, **2020**, 166, 107764	1.7	0
14	Effect of Anion Composition on the Bias Stress Stability in Zn-O-N Thin-Film Transistors. *IEEE Electron Device Letters*, **2020**, 41, 1376-1379	4.4	0
13	Extraction Technique for Flat Band Voltage Using Multi-Frequency C Ⅳ Characteristics in Amorphous InGaZnO Thin-Film-Transistors. *IEEE Electron Device Letters*, **2020**, 41, 1778-1781	4.4	0
12	Observation of Divacancy Formation for ZnON Thin-Film Transistors With Excessive N Content. *IEEE Electron Device Letters*, **2021**, 42, 1006-1009	4.4	0

11	. *IEEE Transactions on Electron Devices*, **2018**, 65, 3243-3249	2.9	0
10	Fabrication of Circadian Light Meter with Non-Periodic Optical Filters to Evaluate the Non-Visual Effects of Light on Humans. *Applied Sciences (Switzerland)*, **2021**, 11, 8283	2.6	0
9	All-Solution-Processed Carbon Nanotube Floating Gate Memories. *ACS Applied Nano Materials*,	5.6	0
8	Electrode-dependent electrical switching characteristics of InGaZnO memristor. *Chaos, Solitons and Fractals*, **2022**, 158, 112106	9.3	0
7	New Type of Ion-Sensitive Field-Effect Transistor with Sensing Region Separate from Gate-Controlled Region. *Journal of Nanoscience and Nanotechnology*, **2017**, 17, 8280-8284	1.3	
6	Investigation of Low-Frequency Noise Properties in High-Mobility ZnON Thin-Film Transistors. *IEEE Electron Device Letters*, **2016**, 1-1	4.4	
5	9.4L: Late-News Paper: Microscopic Mechanism of the Negative Bias and Illumination Stress Instability of Amorphous Oxide TFTs. *Digest of Technical Papers SID International Symposium*, **2012**, 43, 95-97	0.5	
4	P-203L: Late-News Poster: Analysis on AC Stress-Induced Degradation Mechanism of Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistor Inverters. *Digest of Technical Papers SID International Symposium*, **2010**, 41, 1380	0.5	
3	73-3: Invited Paper: Influences of Circadian Illuminances from Lighting and TV on the Human Locomotor Activity, Sleep Disorder, EEG, HRV, and Melatonin Secretion. *Digest of Technical Papers SID International Symposium*, **2020**, 51, 1094-1097	0.5	
2	Deep depletion capacitance□oltage technique for spatial distribution of traps across the substrate in MOS structures. *Solid-State Electronics*, **2020**, 173, 107905	1.7	
1	Modeling and characterization of photovoltaic and photoconductive effects in insulated-gate field effect transistors under optical excitation. *Solid-State Electronics*, **2021**, 186, 108139	1.7	